

Please add the following new claims:

--13. An insulated gate transistor having a gate electrode on a substrate with a gate insulator interposed therebetween, wherein the gate insulator including silicon and oxygen contains both nitrogen atoms and halogen atoms, and wherein nitrogen atom concentration of the gate insulator is within a range of $1 \times 10^{18} \text{ cm}^{-3}$ - $1 \times 10^{20} \text{ cm}^{-3}$ and maximum fluorine atom concentration of the gate insulator is within a range of $1 \times 10^{18} \text{ cm}^{-3}$ - $6 \times 10^{19} \text{ cm}^{-3}$.--


--14. The insulated gate transistor according to claim 2, wherein maximum fluorine atom concentration of the gate insulator is more than $1 \times 10^{19} \text{ cm}^{-3}$.--

--15. The insulated gate transistor according to claim 2, wherein the gate electrode contains boron, and the boron does not diffuse into the substrate.--

--16. The insulated gate transistor according to claim 13, wherein the gate electrode contains boron, and the boron does not diffuse into the substrate.--

--17. The insulated gate transistor according to claim 14, wherein the gate electrode contains boron, and the boron does not diffuse into the substrate.--

--18. The insulated gate transistor according to claim 2, wherein the gate insulator has a film thickness of about 0.5-5 nm.--




--19. The insulated gate transistor according to claim 13, wherein the gate insulator has a film thickness of about 0.5-5 nm.--

--20. The insulated gate transistor according to claim 14, wherein the gate insulator has a film thickness of about 0.5-5 nm.--

--21. The insulated gate transistor according to claim 2, wherein the gate electrode comprises a polycrystalline material that is at least one selected from the group consisting of polysilicon, polycrystalline germanium and polysilicon germanium.--

--22. The insulated gate transistor according to claim 13, wherein the gate electrode comprises a polycrystalline

material that is at least one selected from the group consisting of polysilicon, polycrystalline germanium and polysilicon germanium.--

 --23. The insulated gate transistor according to claim 14, wherein the gate electrode comprises a polycrystalline material that is at least one selected from the group consisting of polysilicon, polycrystalline germanium and polysilicon germanium.--

Attached hereto is a version showing changes made to the application by this Amendment.